



5SDA 10D2303

Old part no. DA 807-970-23

Avalanche Diode

Properties

- low on-state voltage
- avalanche reverse characteristics
- high operational reliability
- suitable for parallel operation

Key Parameters

V_{RRM}	=	2 300	V
I_{FAVm}	=	1 140	A
I_{FSM}	=	13 500	A
V_{TO}	=	0.830	V
r_T	=	0.300	$\text{m}\Omega$

Types

	V_{RRM}
5SDA 10D2303	2 300 V
Conditions:	$T_j = -40 \div 160^\circ\text{C}$, half sine waveform, $f = 50 \text{ Hz}$

Mechanical Data

F_m	Mounting force	$11 \pm 1 \text{ kN}$
m	Weight	0.23 kg
D_s	Surface creepage distance	30 mm
D_a	Air strike distance	20.5 mm

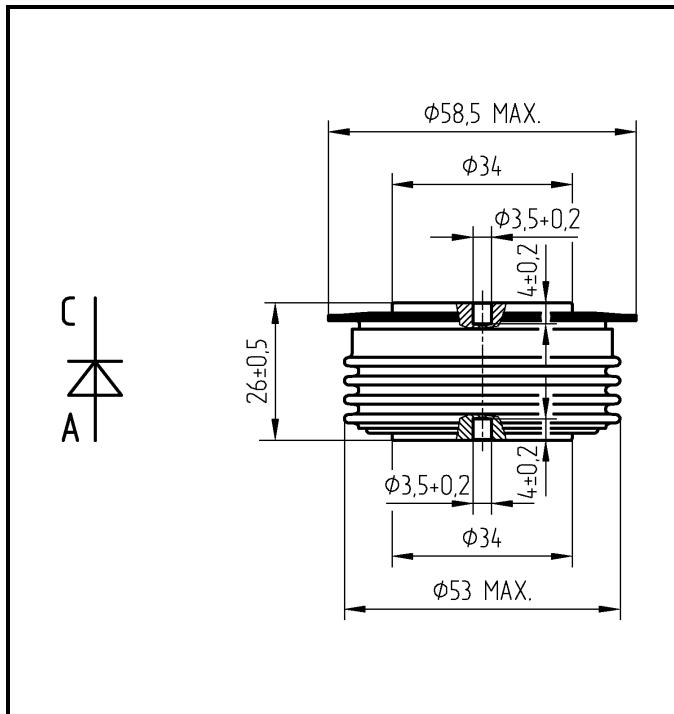


Fig. 1 Case



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Maximum Ratings		Maximum Limits		Unit	
V_{RRM}	Repetitive peak reverse voltage $T_j = -40 \div 160^\circ\text{C}$	2 300		V	
I_{FAVm}	Average forward current $T_c = 85^\circ\text{C}$	1 140		A	
I_{FRMS}	RMS forward current $T_c = 85^\circ\text{C}$	1 790		A	
I_{RRM}	Repetitive reverse current $V_R = V_{RRM}$	50		mA	
I_{FSM}	Non repetitive peak surge current $V_R = 0\text{ V, half sine pulse}$	$t_p = 8.3\text{ ms}$	14 400		A
		$t_p = 10\text{ ms}$	13 500		A
$\int I^2 t$	Limiting load integral $V_R = 0\text{ V, half sine pulse}$	$t_p = 8.3\text{ ms}$	860 000		A^2s
		$t_p = 10\text{ ms}$	911 000		A^2s
P_{RSM}	Maximum avalanche power dissipation rectangular pulse 20 μs	50		kW	
$T_{jmin} \text{ - } T_{jmax}$	Operating temperature range	-40 \div 160		$^\circ\text{C}$	
T_{STG}	Storage temperature range	-40 \div 160		$^\circ\text{C}$	

Unless otherwise specified $T_j = 160^\circ\text{C}$

Characteristics		Value			Unit
		min	typ	max	
V_{T0}	Threshold voltage			0.830	V
	Forward slope resistance $I_F = 1000 \div 3000\text{ A}$			0.300	$\text{m}\Omega$
V_{FM}	Maximum forward voltage $I_{FM} = 1 800\text{ A}$			1.390	V
Q_{rr}	Recovered charge $V_R = 100\text{ V, } I_{FM} = 1 000\text{ A, } di_F/dt = -5\text{ A}/\mu\text{s}$		640		μC

Unless otherwise specified $T_j = 160^\circ\text{C}$

Thermal Parameters			Value	Unit
R_{thjc}	Thermal resistance junction to case	double side cooling	40	K/kW
		anode side cooling	65	
		cathode side cooling	104	
R_{thch}	Thermal resistance case to heatsink	double side cooling	10	K/kW
		single side cooling	20	

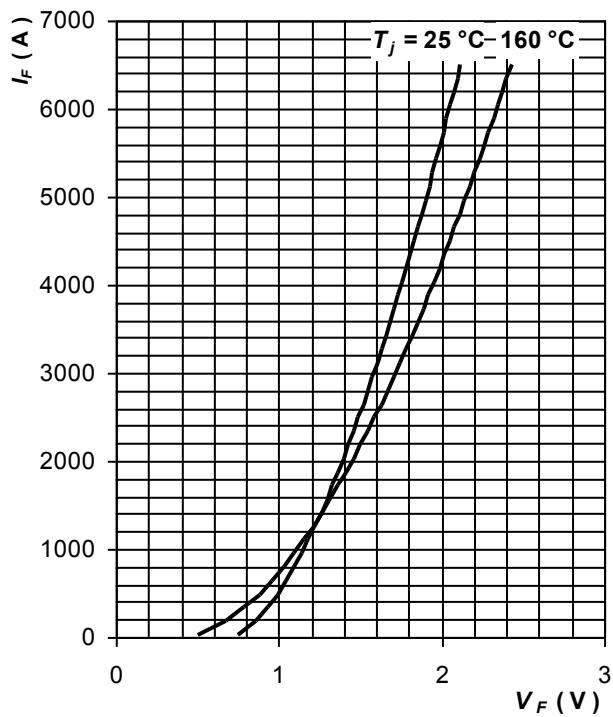
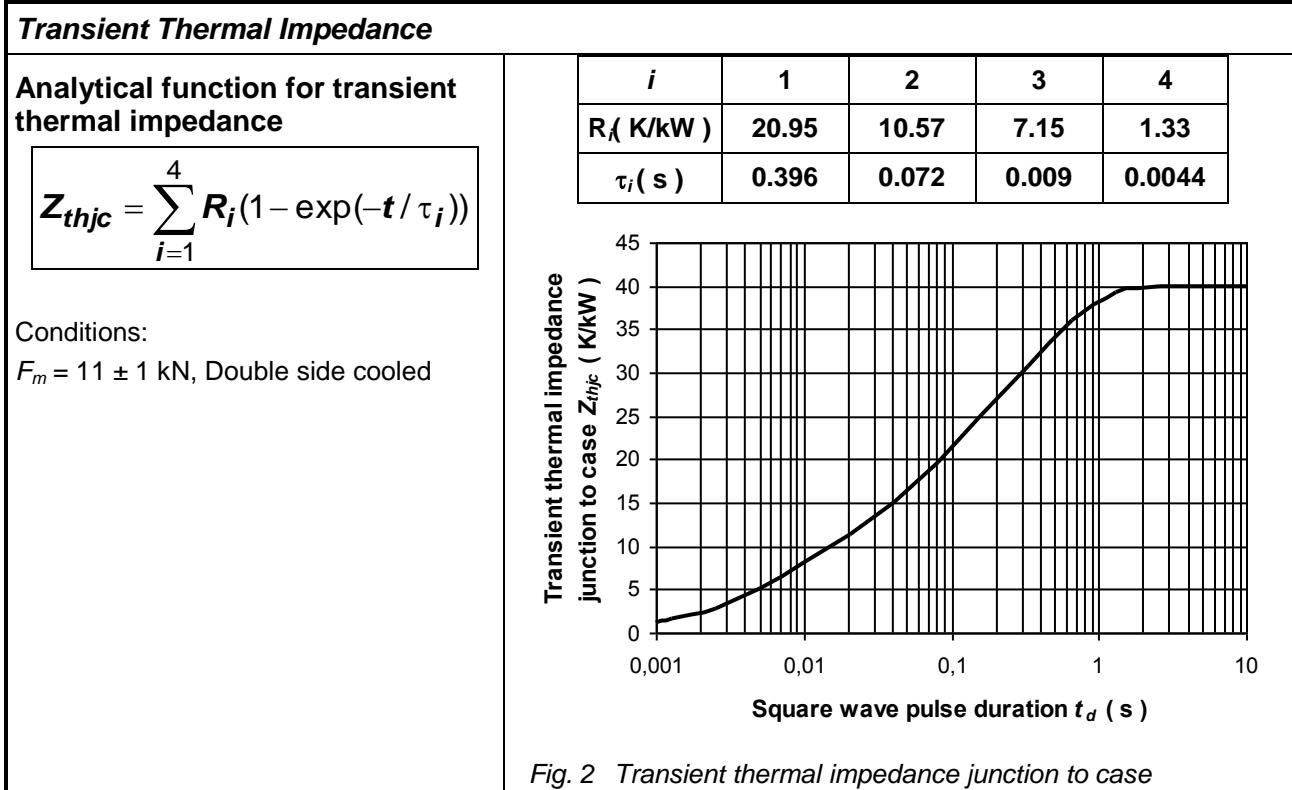


Fig. 3 Maximum forward voltage drop characteristics

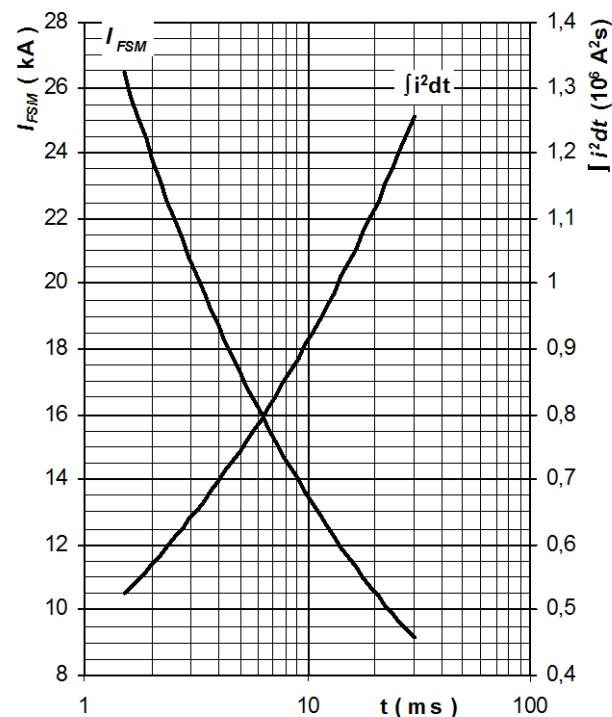


Fig. 4 Surge forward current vs. pulse length, half sine wave, single pulse,
 $V_R = 0 \text{ V}$, $T_j = T_{jmax}$

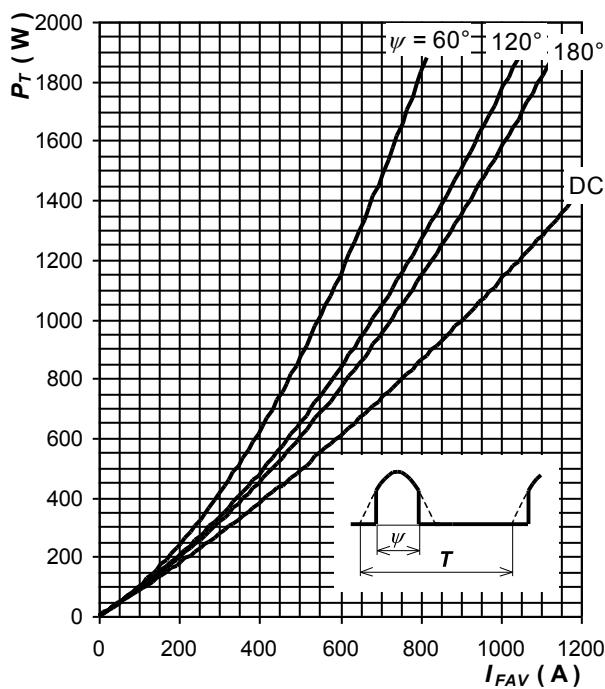


Fig. 5 Forward power loss vs. average forward current, sine waveform, $f = 50$ Hz, $T = 1/f$

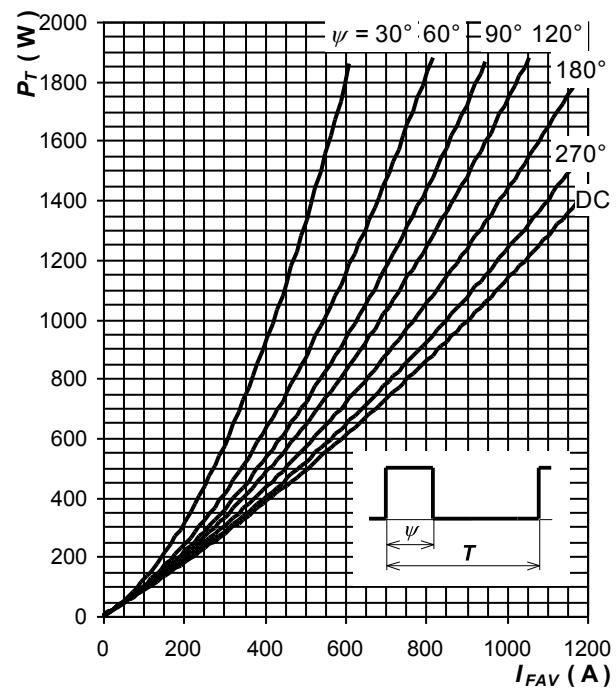


Fig. 6 Forward power loss vs. average forward current, square waveform, $f = 50$ Hz, $T = 1/f$

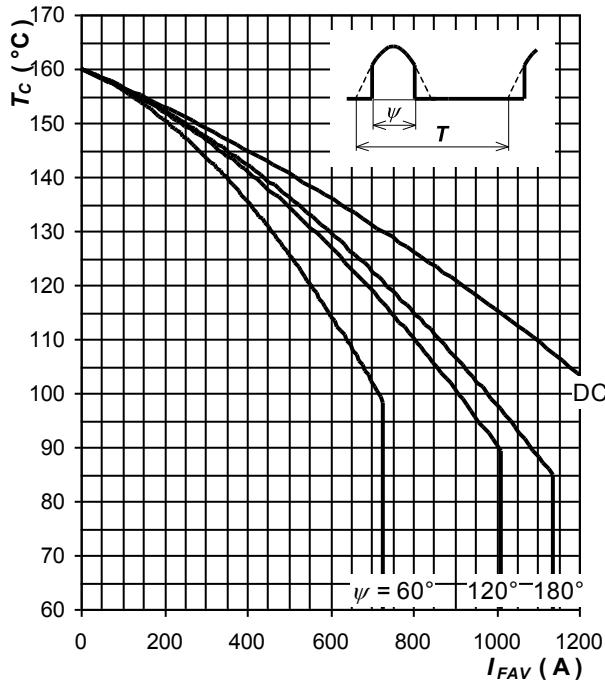


Fig. 7 Max. case temperature vs. aver. forward current, sine waveform, $f = 50$ Hz, $T = 1/f$

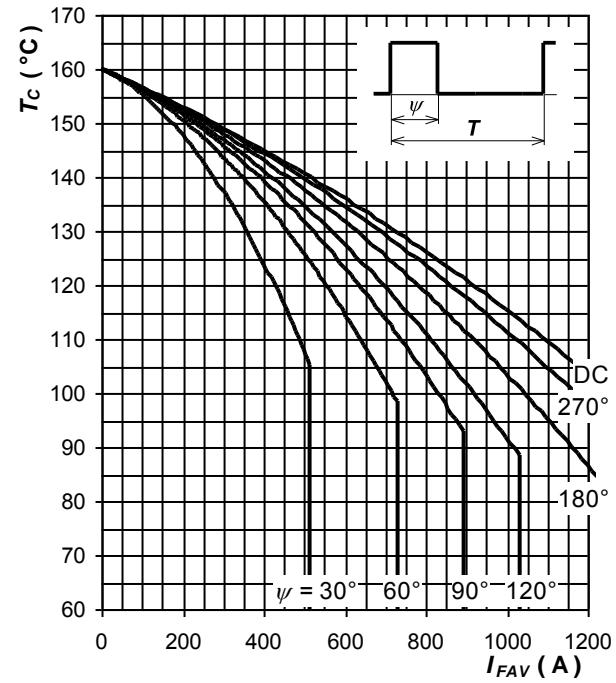


Fig. 8 Max. case temperature vs. aver. forward current, square waveform, $f = 50$ Hz, $T = 1/f$

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